

Features:

- RoHS Compliant
- 150 Watts
- DC 2.7 GHz
- AIN Ceramic
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested

Description:

The A150N50X4B is high performance Aluminum Nitride (AlN) chip termination intended as a cost competitive alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators, and for use in power combiners. The termination is also RoHS compliant!

General Specifications:

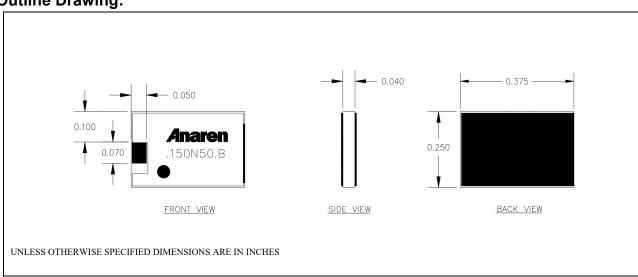
Resistive Element	Thick Film
Substrate	AIN Ceramic
Terminal Finish	Matte Tin over Nickel Barrier
Operating Temperature	-55 to +200°C (see de rating chart)

Electrical Specifications:

Resistance Value Power:	50 Ohms, ± 2% 150 Watts
Frequency Range:	DC – 2.7 GHz
Return Loss	>26dB to 2.0 GHz
	>20dB to 2.7 GHz

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.**

Outline Drawing:

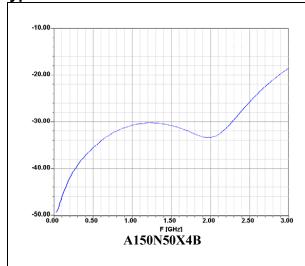


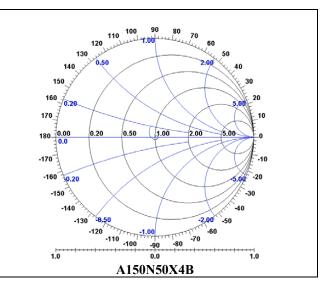
Tolerance is ±0.010", unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. All dimensions in inches.



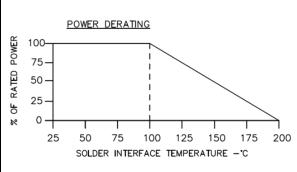


Typical Performance:



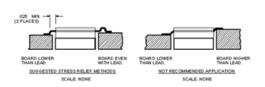


Power de-rating:



*Actual performance could be limited by the solder properties of the application

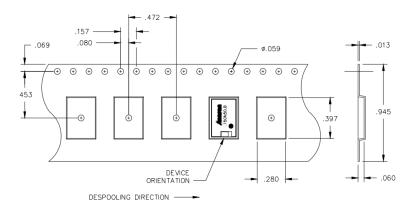
Mounting Footprint:



SUGGESTED MOUNTING PROCEDURE

- MAKE SURE THAT THE DEVICES ARE MOUNTED ON FLAT SURFACES (.001" UNDER THE DEVICE) TO OPTIMIZE THE HEAT TRANSFER.
- POSITION DEVICE ON MOUNTING SURFACE AND SOLDER IN PLACE USING AN APPROPRIATE SOLDER.
- SOLDER LEADS IN PLACE USING AN APPROPRIATE SOLDER TYPE WITH A CONTROLLED TEMPERATURE IRON.

Tape & Reel:



Contact us:

rf&s_support@ttm.com

